SILICON N CHANNEL MOS TYPE

TOSHIBA (DISCRETE/OPTO)

T-39-13

AUDIO FREQUENCY POWER AMPLIFIER APPLICATION.

FEATURES:

. High Breakdown Voltage

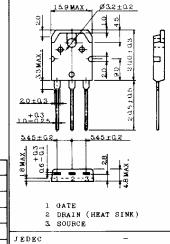
: V_{DSS}=160V

. High Forward Transfoer Admittance : $|Y_{fs}| = 2.0S$ (Typ.)

. Complementary to 2SJ115

Unit in mm

2-16018



MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Drain-Source Voltage	V _{DSS}	160	v
Gate-Source Voltage	V _{GSS}	±20	v
Drain Current	ID	8	A
Power Dissipation (Tc=25°C)	PD	100	W
Channel Temperature	Tch	150	°C
Storage Temperature Range	Tstg	-55 ~150	°c

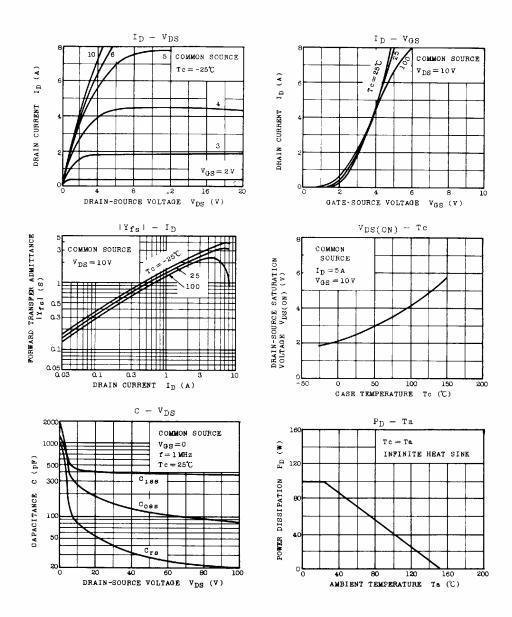
Weight: 4.6g

EIAJ TOSHIBA

ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current	IGSS	V _{DS} =0, V _{GS} =±20V	-	-	±1.0	μA
Drain-Source Breakdwon Voltage	V(BR)DSS	ID=5mA, VGS=0	160	-	-	V
Gate-Source Cut-off Voltage	VGS(OFF) (Note)	V _{DS} =10V, I _D =0.1A	0.8	-	2.8	٧
Drain-Source Saturation Voltage	VDS (ON)	I _D =5A, V _{GS} =10V	-	2.5	7.0	v
Forward Transfer Admittance	Yfs	V _{DS} =10V, I _D =2A	1.0	2.0	-	S
Input Capacitance	Ciss	V _{DS} =10V, V _{GS} =0, f=1MHz	-	430	-	рF
Output Capacitance	Coss	V _{DS} =10V, V _{GS} =0, f=1MHz	-	260	-	рF
Reverse Transfer Capacitance	Crs	V _{DS} =10V, V _{GS} =0, f=1MHz	-	80	-	рF

Note : $V_{GS(OFF)}$ Classification 0 : 0.8~1.6, Y : 1.4~2.8



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